



50V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
	2.6Ω @ V _{GS} = 10V	310mA
50V	3.2Ω @ V _G S = 4.5V	280mA
	5.2Ω @ V _G S = 2.5V	240mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/guality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

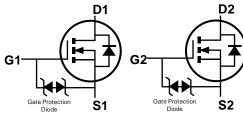
Load Switch

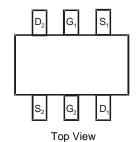
Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)









Top View

Internal Schematic

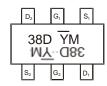
Ordering Information (Note 4)

Part Number	Package	Pa	ncking
Fait Number	Package	Qty.	Carrier
BSS138DWK-7	SOT363	3,000	Reel
BSS138DWK-13	SOT363	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



38D = Product Type Marking Code $\overline{Y}M$ = Date Code Marking \overline{Y} = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	М	N	0	Р	R	S	Т	U
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	50	V	
Gate-Source Voltage	Vgss	±20	V		
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	I _D	310 250	mA	
Maximum Continuous Body Diode Forward Curr	ent (Note 6)	Is	310	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)		I_{DM}	0.9	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.33	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	371	°C/W
Total Power Dissipation (Note 6)		PD	0.49	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	257	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

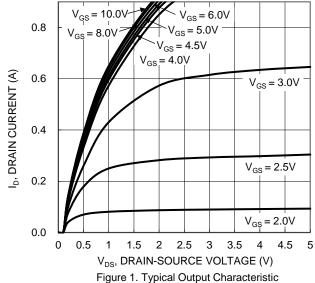
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

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Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)							·		
Drain-Source Breakdown Voltage		BVDSS	50	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$		
Zero Gate Voltage Drain Current TJ	J = +25°C	IDSS	_		1	μΑ	V _{DS} = 50V, V _{GS} = 0V		
Gate-Source Leakage		I _{GSS}	_		±10	μΑ	$V_{GS} = \pm 20V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)									
Gate Threshold Voltage		V _{GS(TH)}	0.5		1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
				1.2	2.6		$V_{GS} = 10V, I_{D} = 0.2A$		
Static Drain-Source On-Resistance		RDS(ON)		1.4	3.2	Ω	$V_{GS} = 4.5V, I_{D} = 0.2A$		
			_	2.9	5.2		$V_{GS} = 2.5V, I_{D} = 0.2A$		
Diode Forward Voltage		VsD	_	0.8	1.2	V	$V_{GS} = 0V, I_{D} = 0.2A$		
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance		Ciss	_	22	_	рF	25)/)/		
Output Capacitance		Coss	_	5	_	pF	V _{DS} = 25V, V _{GS} = 0V -f = 1.0MHz		
Reverse Transfer Capacitance		Crss		4	_	pF	1 – 1.51/11/2		
Gate Resistance		Rg	_	67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (V _{GS} = 4.5V)		Qg		0.4	_	nC			
Total Gate Charge (V _{GS} = 10V)		Qg	_	8.0	_	nC	V _{DS} = 25V, I _D = 0.2A		
Gate-Source Charge		Qgs	_	0.1	_	nC	VDS = 25V, ID = 0.2A		
Gate-Drain Charge		Qgd	_	0.2	_	nC			
Turn-On Delay Time		td(ON)	_	0.4	_	ns			
Turn-On Rise Time		t _R	_	1.2	_	ns	V _{DS} = 25V, V _{GS} = 10V,		
Turn-Off Delay Time		tD(OFF)	_	12.3	_	ns	$R_G = 50\Omega$, $I_D = 0.2A$		
Turn-Off Fall Time		tF	_	7.3	_	ns			
Reverse Recovery Time		trr	_	10.5	_	ns	$I_F = 0.2A$, $di/dt = 100A/\mu s$		
Reverse Recovery Charge		Q _{RR}	_	4	_	nC	$I_F = 0.2A$, $di/dt = 100A/\mu s$		

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





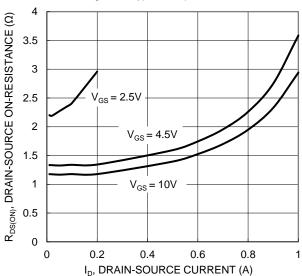


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

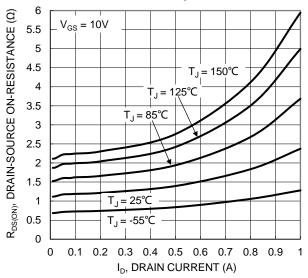


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

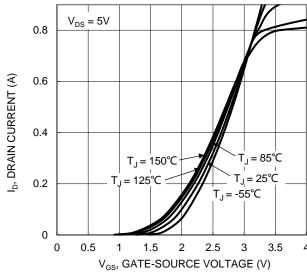
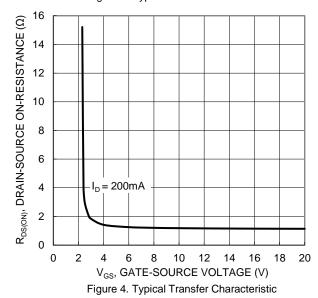


Figure 2. Typical Transfer Characteristic



2.2 RDS(ON), DRAIN-SOURCE ON-RESISTANCE 2 1.8 $V_{GS} = 10V, I_D = 200mA$ (NORMALIZED) 1.6 $V_{GS} = 4.5V, I_D = 200mA$ 1.4 1.2 1 $V_{GS} = 2.5V, I_D = 200mA$ 8.0 0.6 -50 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Junction Temperature



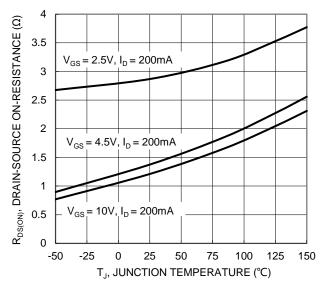


Figure 7. On-Resistance Variation with Junction Temperature

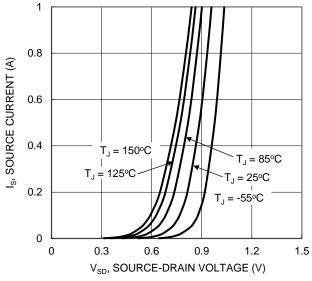


Figure 9. Diode Forward Voltage vs. Current

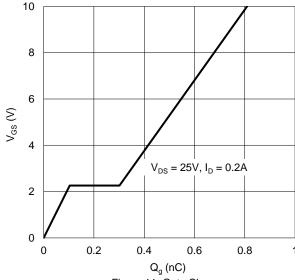


Figure 11. Gate Charge

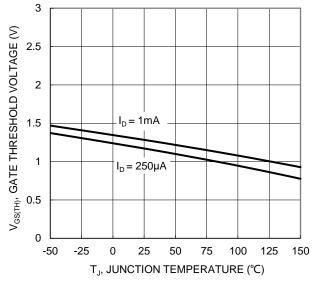
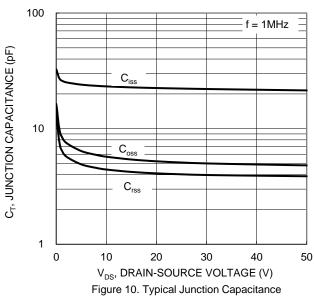
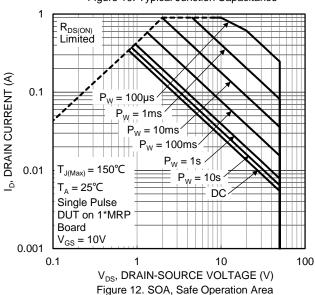


Figure 8. Gate Threshold Variation vs. Junction Temperature







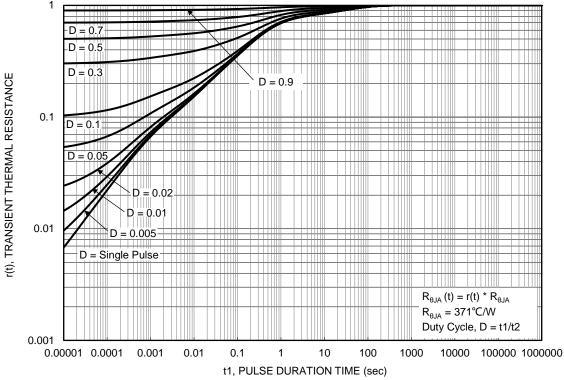
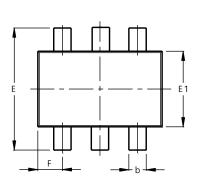


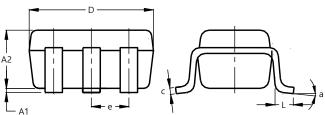
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





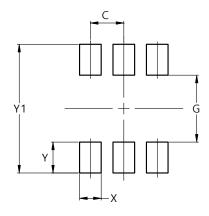
SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	1.00			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	().650 B	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All	Dimen	sions	in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

SOT363



Dimensions	Value		
Dilliensions	(in mm)		
C	0.650		
G	1.300		
Х	0.420		
Υ	0.600		
Y1	2 500		

November 2021

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